• General Description

The AGM628MAP combines advanced trench MOSFET technology with a low resistance package to provide extremely low $R_{DS(ON)}$.

This device is ideal for load switch and battery protection applications.

• Features

- ■ Advance high cell density Trench technology
- ■ Low $R_{DS(ON)}$ to minimize conductive loss
- ■Low Gate Charge for fast switching
- ■Low Thermal resistance
- ■100% Avalanche tested
- ■100% DVDS tested

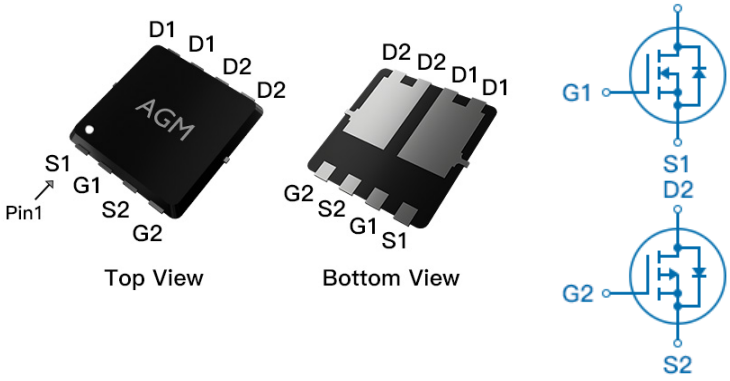
• Application

- ■MB/VGA Vcore
- ■SMPS 2nd Synchronous Rectifier
- ■POL application
- ■BLDC Motor driver

Product Summary

BVDSS	RDSON	ID
60V	30mΩ	21A
-60V	44mΩ	-21A

PDFN3.3*3.3 Pin Configuration



Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
AGM628MAP	AGM628MAP	PDFN3.3*3.3	330mm	12mm	5000

Table 1. Absolute Maximum Ratings (T_A=25°C)

Symbol	Parameter	Rating		Units
		N-Ch	P-Ch	
V_{DS}	Drain-Source Voltage (V_{GS}=0V)	60	-60	V
V_{GS}	Gate-Source Voltage (V_{DS}=0V)	±20	±20	V
I_D	Drain Current-Continuous(Tc=25℃) (Note 1)	21	-21	A
	Drain Current-Continuous(Tc=100℃)	14	-14	A
IDM (pluse)	Drain Current-Pulsed (Note 2)	84	-84	A
P_D	Total Power Dissipation(Tc=25℃)	25	25	W
	Total Power Dissipation(Tc=100℃)	10	10	W
EAS	Avalanche energy (Note 3)	49	65	mJ
TJ,TSTG	Operating Junction and Storage Temperature Range	-55 To 150	-55 To 150	℃

Table 2. Thermal Characteristic

Symbol	Parameter	Typ	Max	Unit
$R_{\theta JA}$	Thermal Resistance Junction-ambient (Steady State)[1]	---	62	℃/W
$R_{\theta JC}$	Thermal Resistance Junction-Case[1]	---	5.0	℃/W

Table 3. N- Channel Electrical Characteristics (TJ=25℃unless otherwisenoted)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
On/Off States						
BVDSS	Drain-Source Breakdown Voltage	VGS=0V ID=250μA	60	--	--	V
IDSS	Zero Gate Voltage Drain Current	VDS=60V,VGS=0V	--	--	1	μA
IGSS	Gate-Body Leakage Current	VGS=±20V,VDS=0V	--	--	±100	nA
VGS(th)	Gate Threshold Voltage	VDS=VGS,ID=250μA	1.2	1.5	2.2	V
gFS	Forward Transconductance	VDS=5V,ID=10A	--	12	--	S
RDS(on)	Drain-Source On-State Resistance	VGS=10V, ID=15A	--	30	36	mΩ
		VGS=4.5V, ID=10A	--	37	45	mΩ
Dynamic Characteristics						
Ciss	Input Capacitance	VDS=30V,VGS=0V, F=1MHZ	--	868	--	pF
Coss	Output Capacitance		--	67	--	pF
Crss	Reverse Transfer Capacitance		--	56	--	pF
Rg	Gate resistance	VGS=0V, VDS=0V,f=1.0MHz	--	1.3	--	Ω
Switching Times						
td(on)	Turn-on Delay Time	VGS=10V,VDS=30V, RL=2.5Ω,RGEN=3Ω	--	4.5	--	nS
tr	Turn-on Rise Time		--	18	--	nS
td(off)	Turn-Off Delay Time		--	14.5	--	nS
tf	Turn-Off Fall Time		--	18	--	nS
Qg	Total Gate Charge	VGS=10V, VDS=30V, ID=3A	--	19	--	nC
Qgs	Gate-Source Charge		--	4.2	--	nC
Qgd	Gate-Drain Charge		--	2.5	--	nC
Source-Drain Diode Characteristics						
ISD	Source-Drain Current(Body Diode)		--	--	21	A
VSD	Forward on Voltage	VGS=0V,IS=15A	--	0.8	1.2	V
trr	Reverse Recovery Time	IF=15A , dI/dt=100A/μs , TJ=25℃	--	--	--	ns
Qrr	Reverse Recovery Charge		--	--	--	nc

Notes 1.The maximum current rating is package limited.

Notes 2.Repetitive Rating: Pulse width limited by maximum junction temperature

Notes 3.EAS condition: TJ=25℃ , VDD=30V,Vgs=10V,ID=14A, L=0.5mH,RG=25ohm

Table 3. P-Channel Electrical Characteristics (TJ=25℃unless otherwisenoted)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
On/Off States						
BVDSS	Drain-Source Breakdown Voltage	VGS=0V ID=-250μA	-60	--	--	V
IDSS	Zero Gate Voltage Drain Current	VDS=-60V,VGS=0V	--	--	-1	μA
IGSS	Gate-Body Leakage Current	VGS=±20V,VDS=0V	--	--	±100	nA
VGS(th)	Gate Threshold Voltage	VDS=VGS,ID=-250μA	-1.2	-1.7	-2.2	V
gFS	Forward Transconductance	VDS=-5V,ID=-10A	--	12	--	S
RDS(on)	Drain-Source On-State Resistance	VGS=-10V, ID=-15A	--	44	67	mΩ
		VGS=-4.5V, ID=-10A	--	56	88	mΩ
Dynamic Characteristics						
Ciss	Input Capacitance	VDS=-30V,VGS=0V, F=1MHZ	--	748	--	pF
Coss	Output Capacitance		--	120	--	pF
Crss	Reverse Transfer Capacitance		--	12	--	pF
Rg	Gate resistance	VGS=0V, VDS=0V,f=1.0MHz	--	4.2	--	Ω
Switching Times						
td(on)	Turn-on Delay Time	VGS=-10V,VDS=-30V, RGEN=3Ω	--	10	--	nS
tr	Turn-on Rise Time		--	6.0	--	nS
td(off)	Turn-Off Delay Time		--	40	--	nS
tf	Turn-Off Fall Time		--	13	--	nS
Qg	Total Gate Charge	VGS=-10V, VDS=-30V, ID=-3A	--	25	--	nC
Qgs	Gate-Source Charge		--	5.8	--	nC
Qgd	Gate-Drain Charge		--	3.1	--	nC
Source-Drain Diode Characteristics						
ISD	Source-Drain Current(Body Diode)		--	--	-21	A
VSD	Forward on Voltage	VGS=0V,IS=-15A	--	-0.8	-1.2	V
trr	Reverse Recovery Time	IF=-15A , dI/dt=100A/μs , TJ=25℃	--	--	--	ns
Qrr	Reverse Recovery Charge		--	--	--	nc

Notes 1.The maximum current rating is package limited.

Notes 2.Repetitive Rating: Pulse width limited by maximum junction temperature Notes

3.EAS condition: TJ=25℃,VDD=-30V,Vgs=-10V,ID=-16A, L=0.5mH,RG=25ohm

N-Channel Typical Characteristics

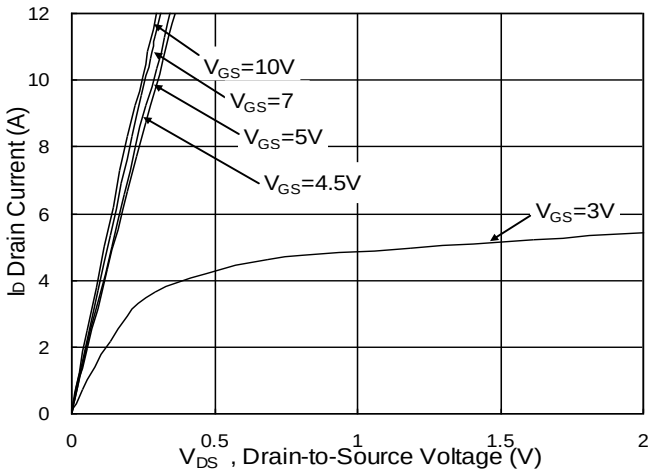


Fig.1 Typical Output Characteristics

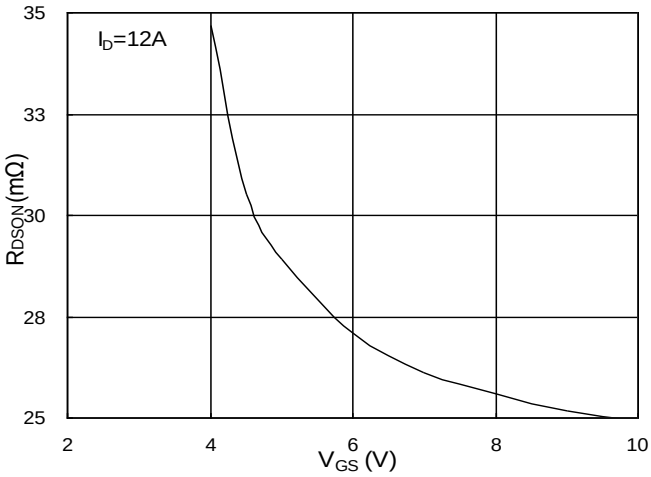


Fig.2 On-Resistance v.s Gate-Source

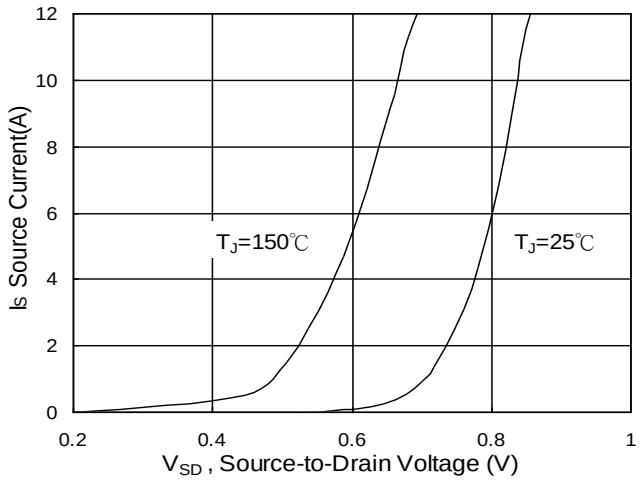


Fig.3 Forward Characteristics of Reverse

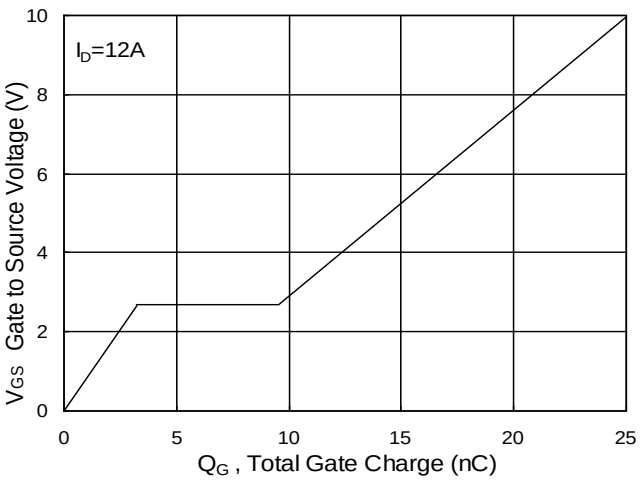


Fig.4 Gate-Charge Characteristics

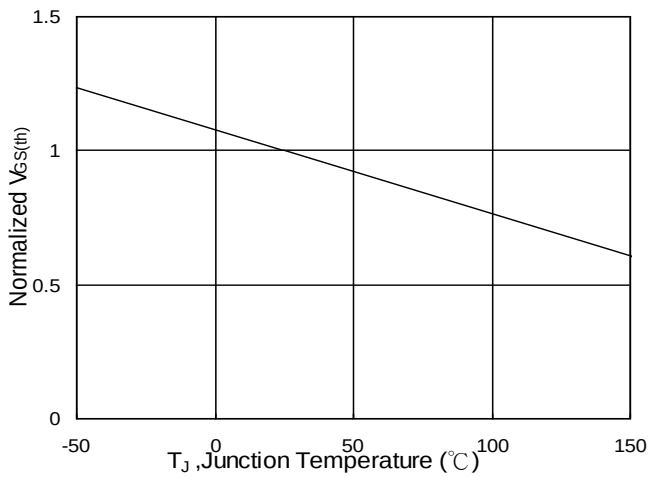


Fig.5 Normalized $V_{GS(th)}$ v.s T_J

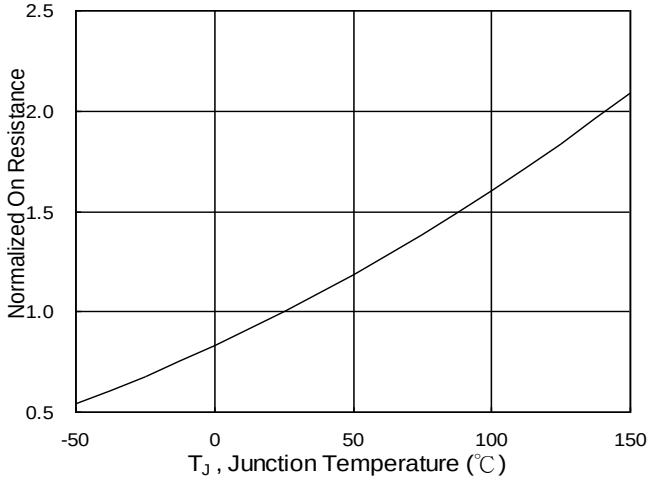


Fig.6 Normalized R_{DSON} v.s T_J

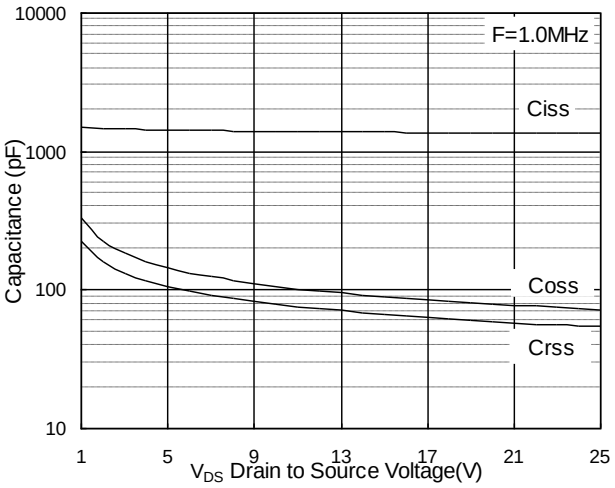


Fig.7 Capacitance

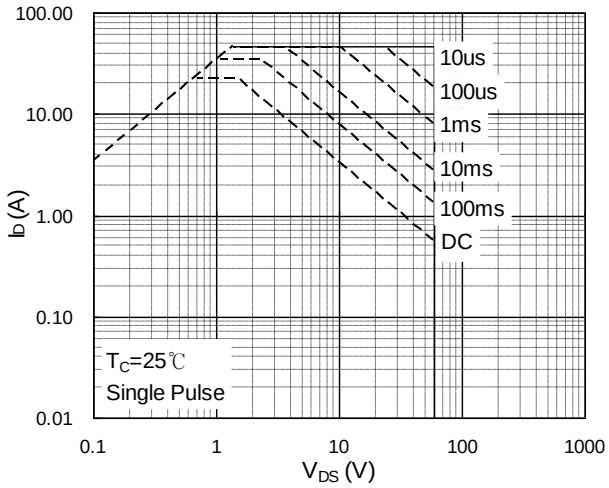


Fig.8 Safe Operating Area

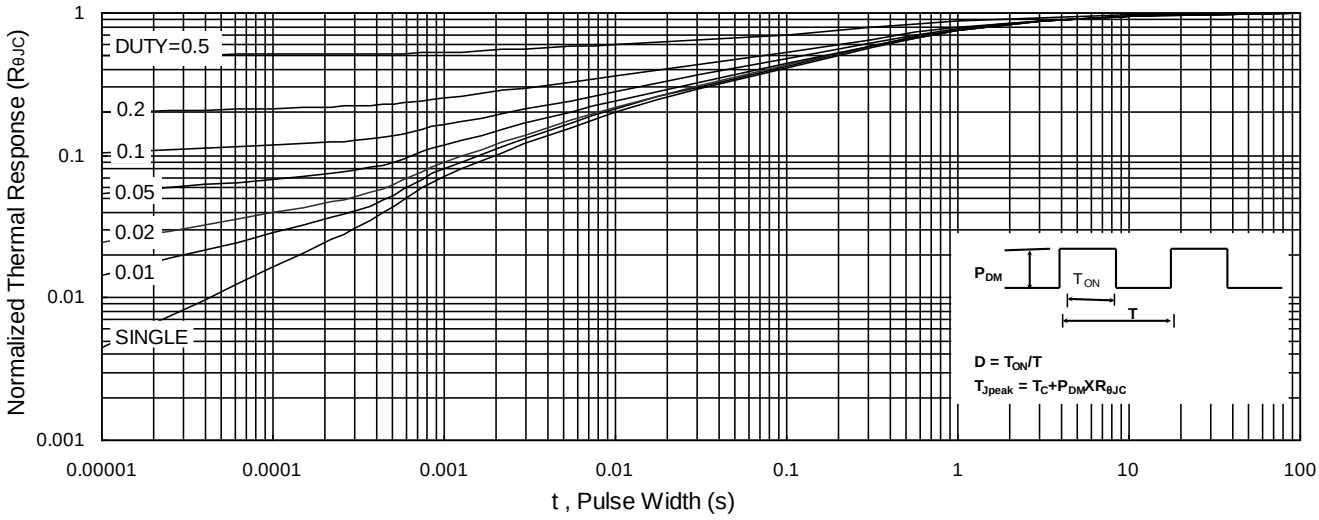


Fig.9 Normalized Maximum Transient Thermal Impedance

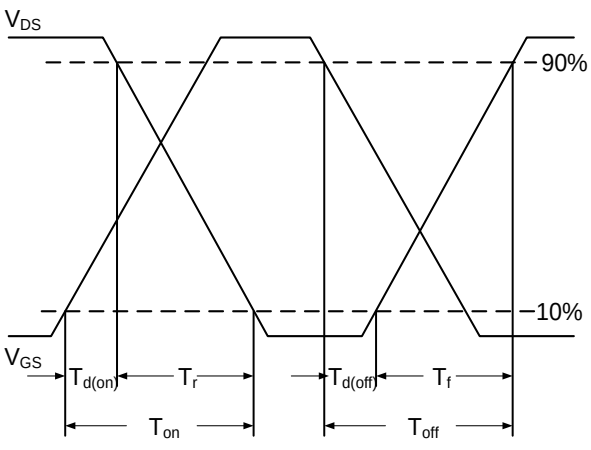


Fig.10 Switching Time Waveform

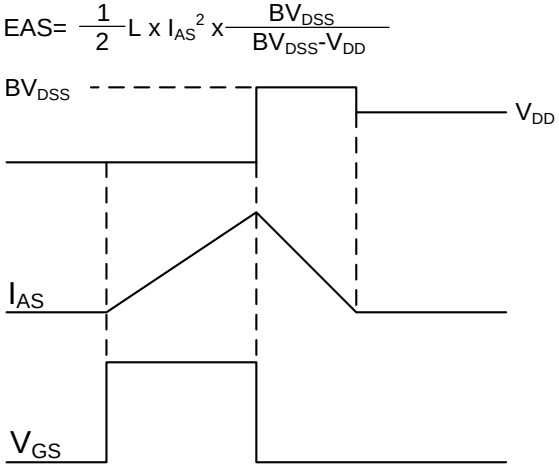


Fig.11 Unclamped Inductive Waveform

P-Channel Typical Characteristics

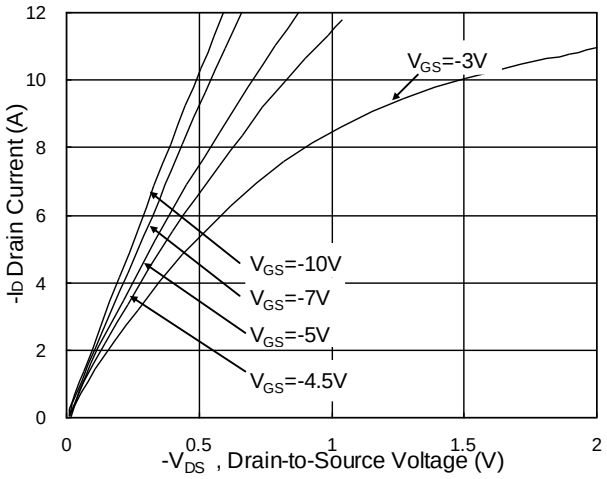


Fig.1 Typical Output Characteristics

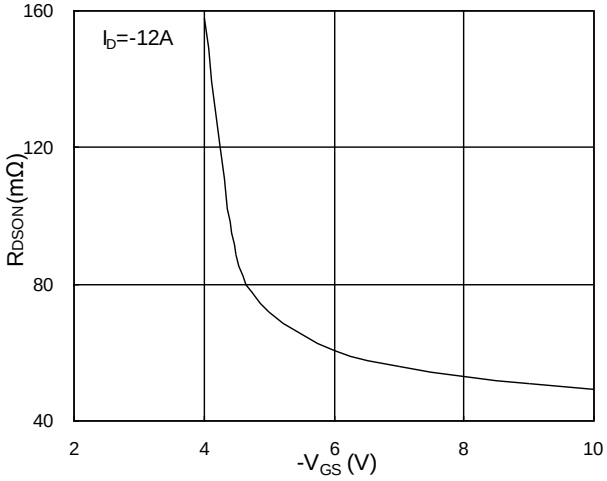


Fig.2 On-Resistance v.s Gate-Source

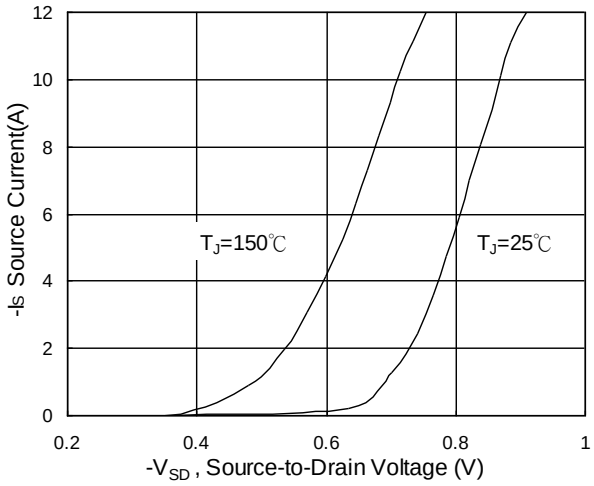


Fig.3 Forward Characteristics of Reverse

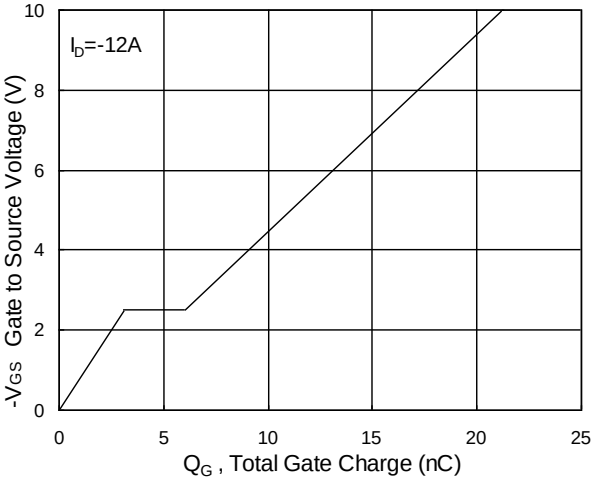


Fig.4 Gate-Charge Characteristics

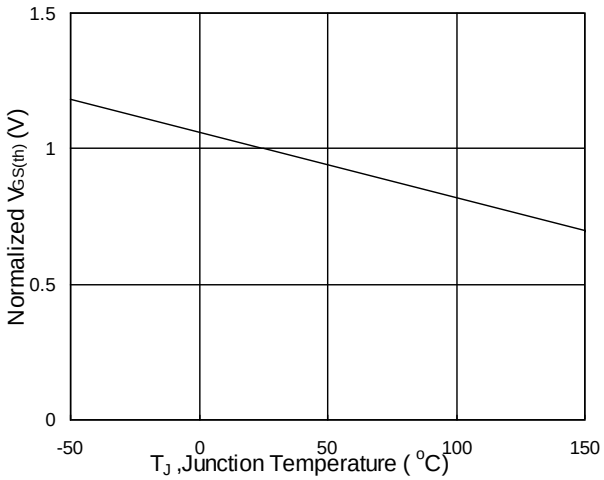


Fig.5 Normalized $V_{GS(th)}$ v.s T_J

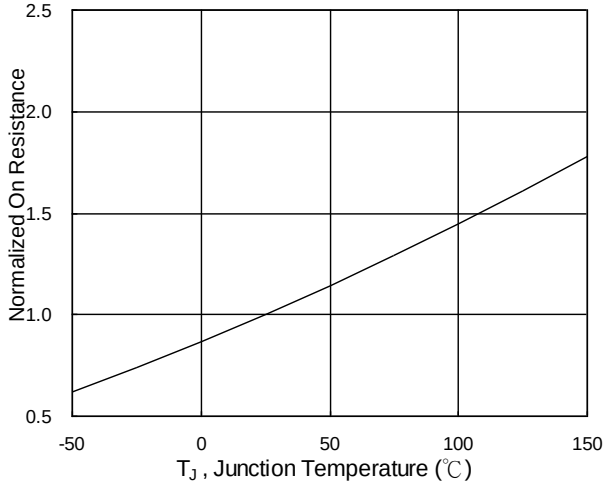


Fig.6 Normalized R_{DSON} v.s T_J

P-Channel Typical Characteristics

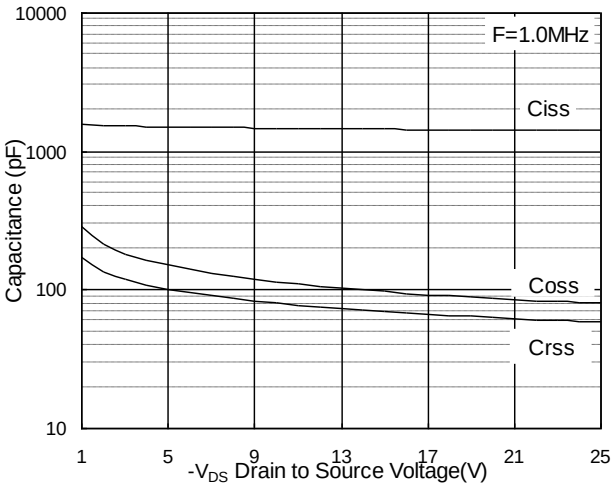


Fig.7 Capacitance

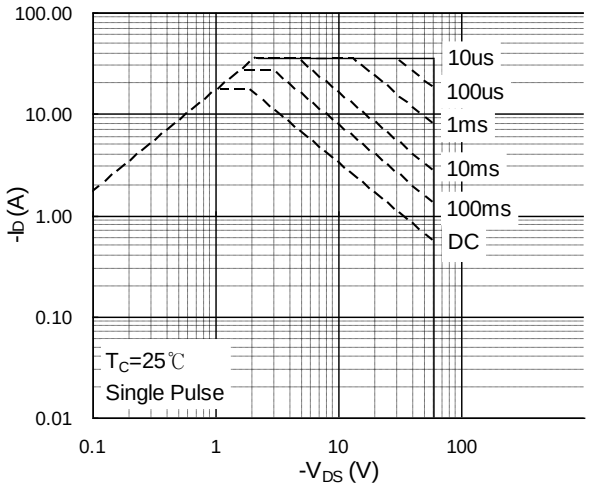


Fig.8 Safe Operating Area

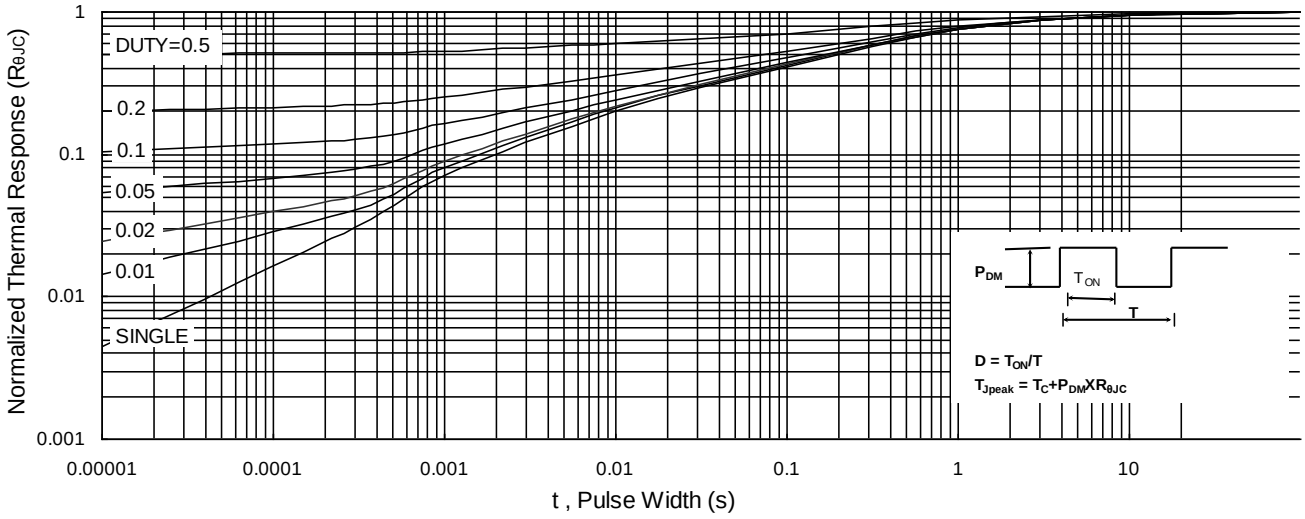


Fig.9 Normalized Maximum Transient Thermal Impedance

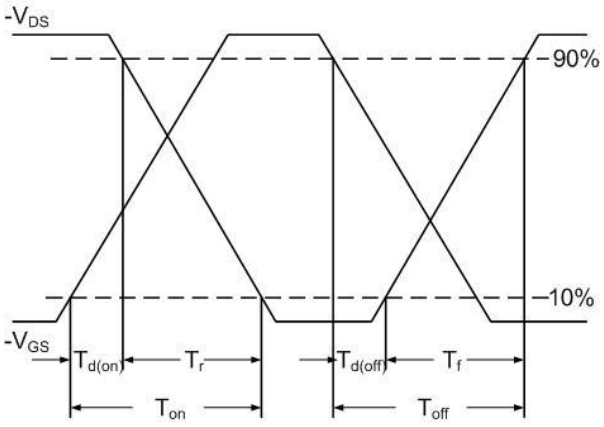


Fig.10 Switching Time Waveform

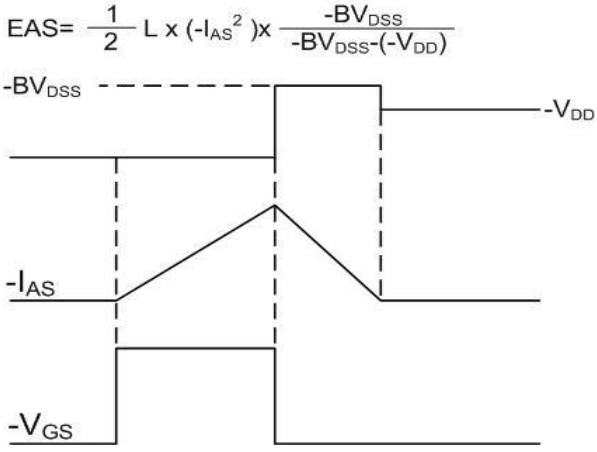
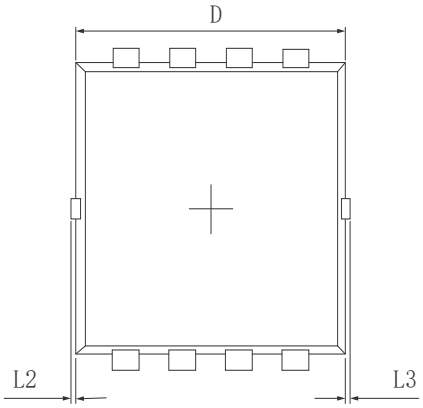
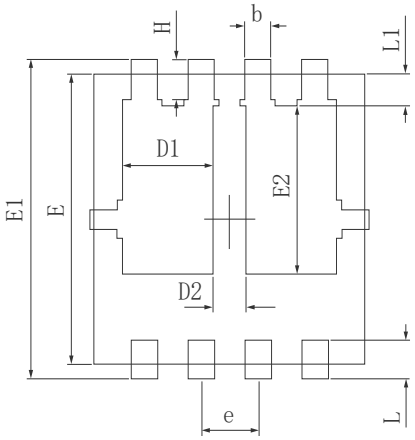
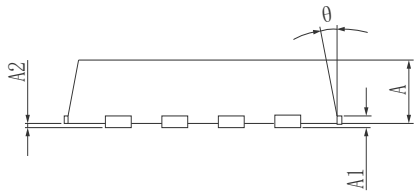


Fig.11 Unclamped Inductive Waveform

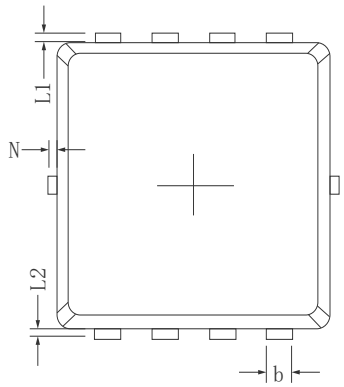
●Dimensions（PDFN3.3*3.3）

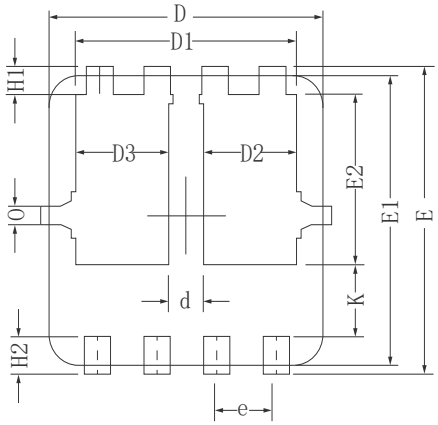


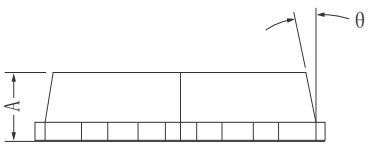


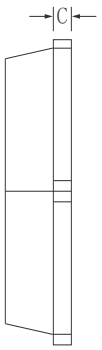


SYMBOL	MILLIMETER	
	MIN	MAX
A	0.700	0.900
A1	0.152REF.	
A2	0~0.05	
D	3.000	3.200
D1	0.935	1.135
D2	0.280	0.480
E	2.900	3.100
E1	3.150	3.450
E2	1.535	1.935
b	0.200	0.400
e	0.550	0.750
L	0.300	0.500
L1	0.180	0.480
L2	0~0.100	
L3	0~0.100	
H	0.315	0.515
θ	8°	12°



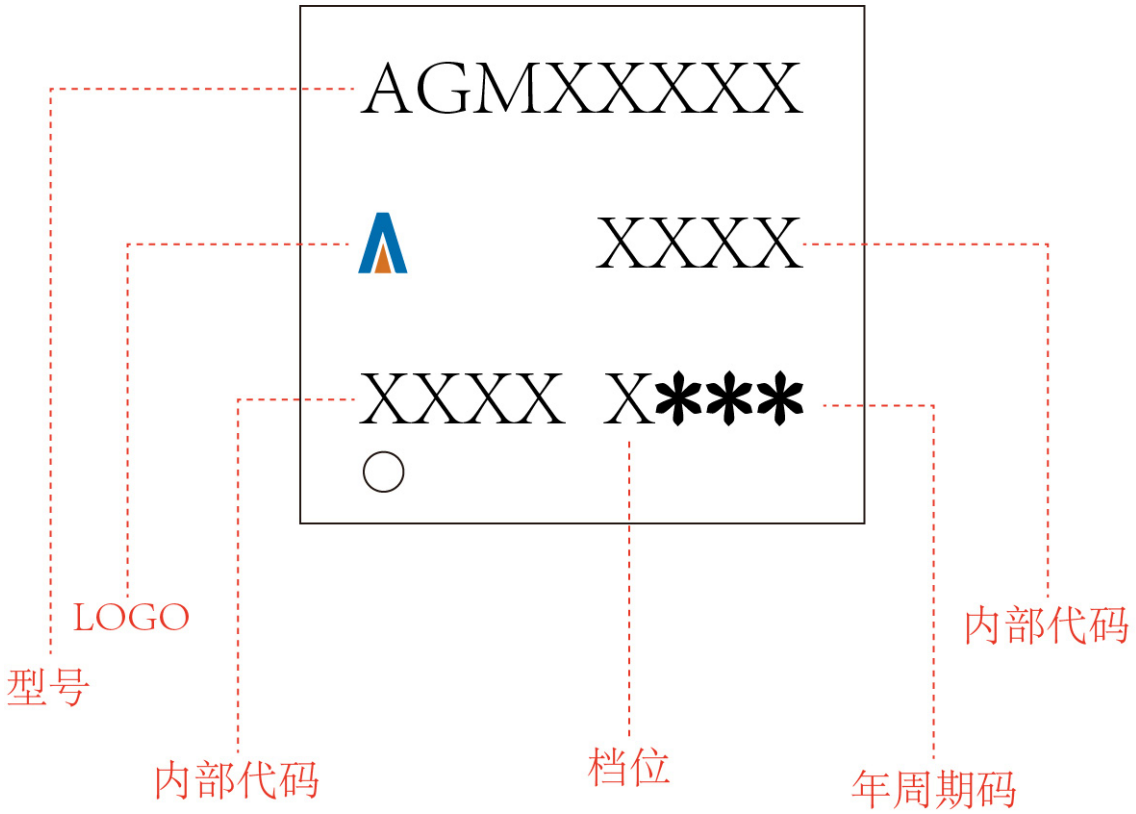






Symbols	Millimeters		
	MIN.	NOM.	MAX.
A	0.65	0.75	0.85
b	0.25	0.30	0.35
C	0.15	0.20	0.25
D	3.00	3.10	3.20
D1	2.40	2.50	2.60
D2/D3	1.00	1.05	1.10
d	0.30	0.40	0.50
E	3.20	3.30	3.40
E1	3.00	3.10	3.20
E2	1.72	1.82	1.92
e	0.65 BSC.		
H1	0.21	0.31	0.41
H2	0.30	0.40	0.50
K	0.67	0.77	0.87
L1/L2	0.10 REF.		
θ	11°	12°	13°
N	0	-	0.15
O	0.2 REF.		

PDFN3.3*3.3
Marking Instructions:



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